



6

Patent Landscape

August 2018

www.relecura.com



#### Introduction

A semiconductor sensor is a device that uses a semiconductor, usually silicon or germanium, to detect traversing charged particles or the absorption of photons. Several thin wafers of the semiconductor material are layered together to form these sensors. In the field of particle physics, these sensors are usually known as silicon detectors. When their sensitive structures are based on a single diode, they are called semiconductor diode detectors. When they contain many diodes with different functions, the more general term semiconductor detector is used. <sup>[1]</sup>

Semiconductor sensors are known for their higher detection efficiency, better spectrometric resolution, enhanced accuracy and low cost. There are different types of semiconductor sensors for determining gas pressure, temperature, voltage and radiation. The important application areas for semiconductor sensors include medical, automotive and aerospace. They have acquired an added importance in recent times due to the emergence of various applications under the umbrella of the "Internet of Things" (IoT).

The patents studied in this report cover semiconductor sensors and their applications. We analyzed a total of 25,667 currently active published patent applications for the study, of which 16,587 are granted. Unless otherwise stated, the report displays numbers for published patent applications. The analytics are presented in the various charts and tables that follow. These include the following,

- Published Applications Summary
- Published Applications Growth
- Top Patent Holders
- Top Patent Holders Analysis
- Top Patent Holders Portfolio Similarity
- Published Applications By Jurisdiction
- Top CPC Codes
- Top Patent Holders Portfolio Growth

- Top Patent Holders Assets by Jurisdiction
- Top Jurisdictions Growth
- Top CPC Codes Growth
- Top Patent Holders Patent Quality
- Key Technologies Analysis
- Application Areas Top Patent Holders
- Taxonomy
- Taxonomy (Tabular)

#### Insights

- The published patent applications in semiconductor sensors have shown a steady upward trend.
- The US leads as the jurisdiction with the largest number of published patent applications. The combined published patents in China-Japan-Taiwan-Korea account for around half of all the published applications in this area.
- Most of the leading patent holders have followed the policy of filing in the U.S. in addition to their home countries, indicating the importance of the U.S. market.
- Among the top patent holders the portfolios of Sony, Samsung and TSMC have shown the most significant growth in recent years in the 2015-2017 period.

#### References

- 1. <u>Semiconductor detector</u> (Wikitronics)
- 2. <u>Semiconductor detector</u> (Wikipedia)
- 3. <u>Semiconductor sensors</u> [PDF] (Hall.G)



#### **Published Applications - Summary**

Total 25,60	documents count (Applicat 67	ions)		
PUBLICATION TYPES	IP TYPES		PATENT BY STAR RA	TING
8,712 16,587	24,685 950		2.17	
Applications • Grants	Invention	I.	☆☆☆☆☆	40
	1 Top Patent Hole	der SONY (1,011)	☆☆☆☆☆	362
Peak Year of Activity	🐣 : No of technolog	nies 330	☆☆☆☆☆	5,782
2017 (3,190)			$\Rightarrow$	17,110
1 Top Active Jurisdiction	Top Rated	Top Cited	****	2,373
US (9,009)	U \$8773336B2 (5)	U\$7453065B2 (2,782	)	1 de 1

#### Published Applications - Growth



## Published Applications - Top 20 Patent Holders

Ultimate Patent Holder	# Applications	Ultimate Patent Holder	# Applications
SONY	1,011	STMICROELECTRONICS	412
SAMSUNG	836	INFINEON	368
TAIWAN SEMICONDUCTOR (TSMC)	750	TOSHIBA	336
PANASONIC	712	PHILIPS	284
OMNIVISION TECHNOLOGIES	594	SHARP	273
FUJIFILM	584	SIEMENS	260
DENSO	556	MITSUBISHI	247
HITACHI	497	APTINA IMAGING	226
CANON	451	GE	226
BOSCH	436	AZBIL	225

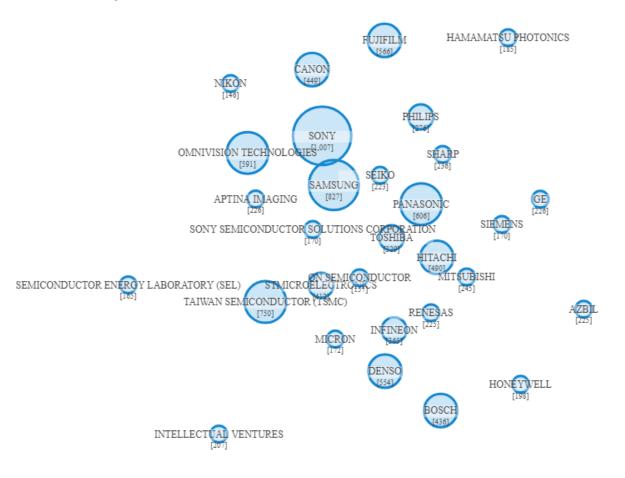


#### **Top Patent Holders - Analysis**

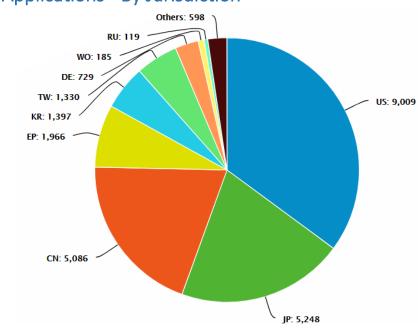
Patent Holders	Applications	Grants	Technologies	Sub Technologies	Geographies
SONY	558	436	electric elements - semiconductor devices (987), pictorial communication (778), optical elements (103), coders & decoders (37), photography - camera (31)	multiple semiconductor or solid state devices components formed on a common substrate (967), hardware or software aspects of tv signals (754), semiconductor devices sensitive to infra-red, light, electromagnetic or corpuscular radiation, converting radiation into electrical energy (213), connecting/disconnecting semiconductor bodies (189), manufacturing or treatment of ics and semiconductor devices (180)	JP (468) , US (239) , CN (127) , KR (67) , TW (48)
SAMSUNG	289	532	electric elements - semiconductor devices (758), pictorial communication (335), optical elements (47), digital data processing (32), measurement by radio waves (32)	multiple semiconductor or solid state devices components formed on a common substrate (673), hardware or software aspects of tv signals (319), semiconductor devices sensitive to infra-red, light, electromagnetic or corpuscular radiation, converting radiation into electrical energy (237), connecting/disconnecting semiconductor bodies (169), manufacturing or treatment of ics and semiconductor devices (142)	US (350) , KR (273) , CN (74) , JP (73) , EP (29)
TAIWAN SEMICONDUCTOR (TSMC)	150	600	electric elements - semiconductor devices (735), pictorial communication (65), mems manufacturing (60), mems devices (55), greentech - reduction & transmission of greenhouse gases (27)	multiple semiconductor or solid state devices components formed on a common substrate (666), manufacturing or treatment of ics and semiconductor devices (281), semiconductor devices sensitive to infra-red, light, electromagnetic or corpuscular radiation, converting radiaiton into electrical energy (222), connecting/disconnecting semiconductor bodies (189), details of semiconductor devices (130)	US (397) , CN (158) , TW (110) , KR (54) , JP (16)
PANASONIC	432	164	electric elements - semiconductor devices (518), pictorial communication (194), measurement - speed (190), measurement - pressure (122), mems devices (53)	multiple semiconductor or solid state devices components formed on a common substrate (246), multistep manufacturing process for rectifiers, oscillators, capacitors and resistors (212), measuring acceleration, deceleration, shock (189), hardware or software aspects of tv signals (176), measuring fluid pressure by electric or magnetic pressure-sensitive elements (118)	JP (460) , US (64) , EP (36) , CN (23) , TW (9)
OMNIVISION TECHNOLOGIES	124	450	electric elements - semiconductor devices (574), pictorial communication (223), optical elements (35), photography - camera (16), digital data processing (10)	multiple semiconductor or solid state devices components formed on a common substrate (570), hardware or software aspects of tv signals (218), semiconductor devices sensitive to infra-red, light, electromagnetic or corpuscular radiation, converting radiation into electrical energy (129), connecting/disconnecting semiconductor bodies (78), manufacturing or treatment of ics and semiconductor devices (68)	US (182) , CN (165) , TW (139) , EP (73) , JP (15)

#### Topic Map – Top Patent Holders – Portfolio Similarity

- The bubble size corresponds to the total number of patent applications held.
- The bubble proximity corresponds to the similarity of each of the company portfolios in terms of technologies covered.







## Published Applications - By Jurisdiction

## Published Applications - Top 20 CPC Codes

Class Code	Description	# Applications
H01L 27/14	Multiple semiconductor or solid state devices components formed on a common substrate >> including semiconductor components sensitive to infra-red radiation, light, electromagnetic radiation of shorter wavelength, or corpuscular radiation and specially adapted either for the conversion of the energy of such radiation into electrical energy or for the control of electrical energy by such radiation	7,763
H01L 2224/01	Connecting/disconnecting semiconductor bodies >> Means for bonding being attached to, or being formed on, the surface to be connected, e.g. chip-to-package, die-attach, "first-level" interconnects; Manufacturing methods related thereto	4,965
H04N 5/30	Hardware or software aspects of TV signals >> Transforming light or analogous information into electric information	2,627
H01L 2924/10	Connecting/disconnecting semiconductor bodies >> Details of semiconductor or other solid state devices to be connected	2,447
H01L 2924/15	Connecting/disconnecting semiconductor bodies >> Details of package parts other than the semiconductor or other solid state devices to be connected	2,390
H01L 2224/73	Connecting/disconnecting semiconductor bodies >> Means for bonding being of different types provided for in two or more of groups	2,139



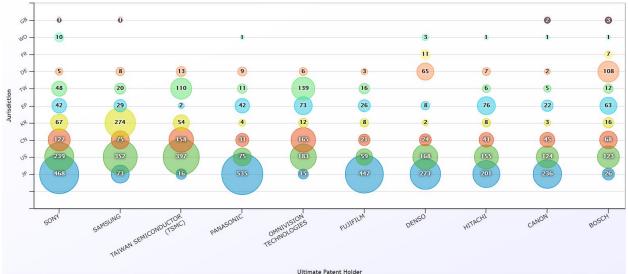
Class Code	Description	# Applications
H01L 2924/0001	Connecting/disconnecting semiconductor bodies >> Technical content checked by a classifier	1,750
H01L 24/01	Connecting/disconnecting semiconductor bodies >> Means for bonding being attached to, or being formed on, the surface to be connected, e.g. chip-to-package, die-attach, "first-level" interconnects; Manufacturing methods related thereto	1,627
G01T 1/16	Measuring and detecting X-radiation, gamma, corpuscular, cosmic, or neutron radiation >> Measuring radiation intensity	1,552
H01L 31/02	Semiconductor devices sensitive to infra-red, light, electromagnetic or corpuscular radiation, converting radiation into electrical energy >> Details	1,397
G01L 9/0041	Measuring fluid pressure by electric or magnetic pressure- sensitive elements >> Transmitting or indicating the displacement of flexible diaphragms	1,212
H01L 2924/01	Connecting/disconnecting semiconductor bodies >> Chemical elements	1,087
G01P 15/02	Measuring acceleration, deceleration, shock >> by making use of inertia forces ; using solid seismic masses	1,040
H01L 2224/80	Connecting/disconnecting semiconductor bodies >> Methods for connecting semiconductor or other solid state bodies using means for bonding being attached to, or being formed on, the surface to be connected	1,038
H01L 21/02	Manufacturing or treatment of ICs and semiconductor devices >> Manufacture or treatment of semiconductor devices or of parts thereof	994
H04N 5/222	Hardware or software aspects of TV signals >> Studio circuitry; Studio devices; Studio equipment ; ; Cameras comprising an electronic image sensor, e.g. digital cameras, video cameras, TV cameras, video cameras, camcorders, webcams, camera modules for embedding in other devices, e.g. mobile phones, computers or vehicles	977
H01L 31/08	Semiconductor devices sensitive to infra-red, light, electromagnetic or corpuscular radiation, converting radiation into electrical energy >> in which radiation controls flow of current through the device, e.g. photoresistors	956
B81B 2201/02	Specific applications of micro-electromechanical systems >> Sensors	942
H01L 2924/30	Connecting/disconnecting semiconductor bodies >> Technical effects	929
B81C 1/00015	Manufacture or treatment of micro-structures on or in substrate >> for manufacturing microsystems	903



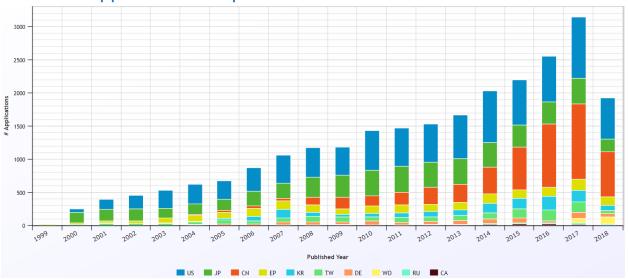
							- C															
	BOSCH	0	1	2	4	11	8	13	14	13	13	15	32	30	34	37	40	54	35	49	31	
	CANON	1	9	12	38	13	17	24	25	21	13	12	12	20	23	22	44	42	38	46	17	- 50
	HITACHI	1	9	п	9	25	16	16	25	36	37	27	26	28	31	17	50	38	28	34	33	
Holder	- DENSO	1	3	п	17	13	22	23	24	35	37	43	43	37	40	36	37	41	31	39	21	- 100
ţ	FUJIFILM	1	14	7	7	15	15	25	53	67	36	53	45	61	42	21	40	36	26	13	6	
ate Date		2	2	7	12	7	10	14	21	27	19	23	24	30	27	52	62	62	79	68	45	- 150
otemit())	PANASONIC	1	43	34	31	21	28	29	47	46	58	45	73	60	44	33	41	21	24	23	8	- 200
	- TAIWAN SEMICONDUCTOR (TSMC)	0	3	8	п	9	8	3	5	п	20	21	18	23	23	49	79	83	149	160	67	
	- SAMSUNG	0	1	5	1	1	5	14	34	51	47	48	47	34	42	53	54	95	120	114	66	
	- SONY	0	13	29	24	32	27	21	30	18	36	45	36	61	49	60	50	105	115	164	92	
	-	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008 Publish	2009 ed Year	2010	2011	2012	2013	2014	2015	2016	2017	2018	Å 1/1 ▼

#### Published Applications – Top 10 Patent Holders – Portfolio Growth



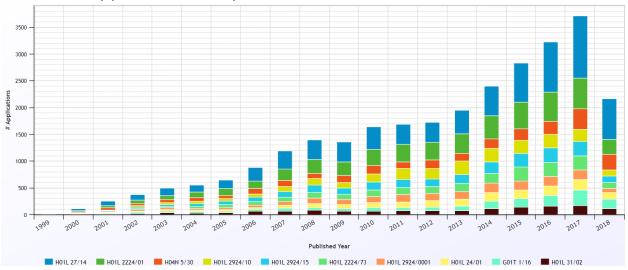






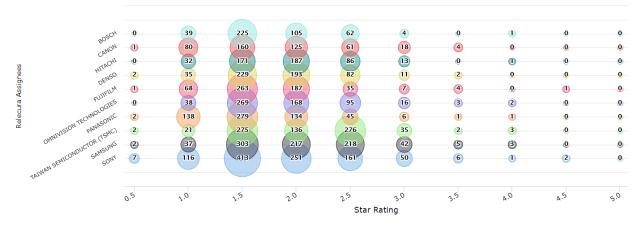
## Published Applications – Top 10 Jurisdictions - Growth

#### Published Applications – Top 10 CPC Codes – Growth





#### Patent Quality – Top 10 Patent Holders (Relecura Star Rating on a scale of 5)



## Key Technologies - Analysis

Technologies	Applications	Grants	Patent Holders	Sub Technologies	Geographies
electric elements - semiconductor devices	6118	11488	SONY (987), SAMSUNG (758), TAIWAN SEMICONDUCTOR (TSMC) (735), OMNIVISION TECHNOLOGIES (574), PANASONIC (518)	multiple semiconductor or solid state devices components formed on a common substrate (12289), connecting/disconnecting semiconductor bodies (5988), hardware or software aspects of tv signals (5040) , semiconductor devices sensitive to infra-red, light, electromagnetic or corpuscular radiation, converting radiation into electrical energy (4575), manufacturing or treatment of ics and semiconductor devices (4058)	US (6045) , JP (4265) , CN (2981) , EP (1265) , TW (1252)
pictorial communication	2239	3651	SONY (778) , FUJIFILM (351) , SAMSUNG (335) , CANON (310) , OMNIVISION TECHNOLOGIES (224)	hardware or software aspects of tv signals (5588), multiple semiconductor or solid state devices components formed on a common substrate (5221), semiconductor devices sensitive to infra-red, light, electromagnetic or corpuscular radiation, converting radiation into electrical energy (1402), connecting/disconnecting semiconductor bodies (775), colour tv details (702)	JP (2055) , US (1976) , CN (659) , EP (381) , KR (338)
measurement - pressure	1123	1981	DENSO (272) , BOSCH (162) , AZBIL (139) , PANASONIC (122) , INFINEON (109)	measuring fluid pressure by electric or magnetic pressure-sensitive elements (2758), details, accessories, apparatus for measuring pressure of fluent medium (1169), multistep manufacturing process for rectifiers, oscillators, capacitors and resistors (949), connecting/disconnecting semiconductor bodies (559), measuring force or stress (525)	US (842) , CN (774) , JP (772) , EP (290) , DE (178)
measurement - radiation	1098	1857	PHILIPS (204) , GE (188) , HITACHI (181) , FUJIFILM (133) , SIEMENS (124)	measuring and detecting x-radiation, gamma, corpuscular, cosmic, or neutron radiation (2991), multiple semiconductor or solid state devices components formed on a common substrate (807), semiconductor devices sensitive to infra-red, light, electromagnetic or corpuscular radiation, converting radiation into electrical energy (723), radiation diagnosis apparatus (850), hardware or software aspects of tv signals (447)	US (896) , JP (729) , CN (474) , EP (433) , KR (114)
measurement by radio waves	958	1184	AZBIL (84) , BOSCH (56) , HAMAMATSU PHOTONICS (42) , CONTINENTAL (41) , AUDI (40)	detecting the presence, distance or velocity of object using reflection or reradiation of em waves (1575), details of the systems using reflection or reradiation of waves (1348), detecting the presence, distance or velocity of object using reflection or reradiation of radio waves (415), measuring distances in line of sight and optical rangefinders (267), measurements using optics between ir and uv (245)	CN (771) , US (547) , JP (251) , EP (235) , DE (130)

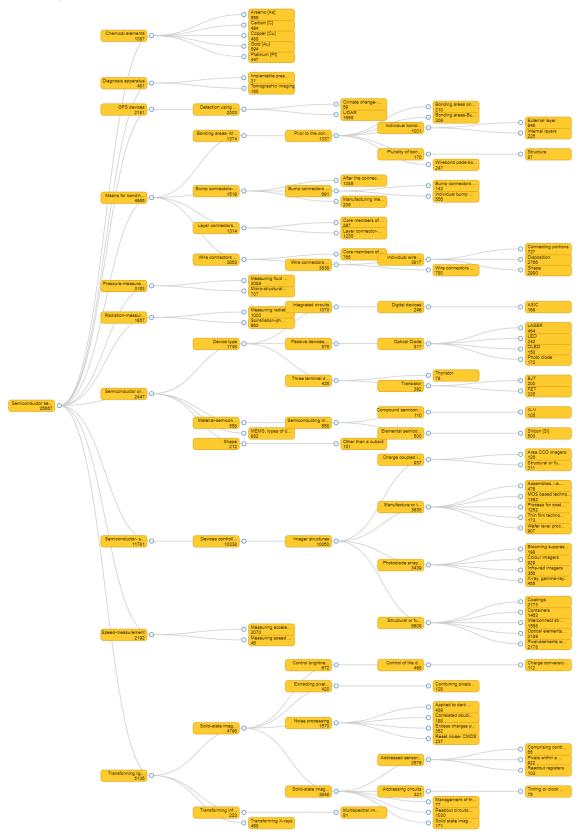


## Application Areas – Top Patent Holders

Areas	# Applications	Top patent holders
-		(# Applications)
Medical	1562	PHILIPS (134)
		GE (123)
		SIEMENS (103)
		HITACHI (74)
		TOSHIBA (54)
Automotive	926	BOSCH (53)
		PORSCHE (42)
		CONTINENTAL (34)
		DENSO (34)
		HITACHI (20)
Aerospace	266	CONTINENTAL (8)
		IMAGE INSIGHT INC (8)
		BOEING (7)
		HONEYWELL (5)
		ZHEJIANG UNIVERSITY OF
		TECHNOLOGY (5)
Robots	122	BASF (7)
		TRINAMIX GMBH (7)
		NDSU RES FOUNDATION (4)
		BENEWAKE (BEIJING)
		PHOTONIC TECH CO LTD (3)
		CONTINENTAL (3)
Military & Defense	106	IMAGE INSIGHT INC (7)
-		LOCKHEED MARTIN (6)
		ZHEJIANG UNIVERSITY OF
		TECHNOLOGY (5)
		AIRBUS (3)
		BOEING (3)









# Taxonomy (Tabular-1)

Т		-	1		
		Arsenic [As]			
		Carbon [C]			
	Chemical elements	Copper [Cu]			
		Gold [Au]			
		Platinum [Pt]			
Г	Diagnosis apparatus	Implantable pressure measuring sensor			
		Tomographic imaging			
$\vdash$			Climate shares LIDAD sustan	г	
Ģ	GPS devices	Detection using reflection or	Climate change- LIDAR system	-	
$\vdash$		reradiation of EM waves	LIDAR	Desitive second states and	1
				Bonding areas on chip-scale packages	
				Bonding areas-Bump	-
		Bonding areas- Manufacturing	Prior to the connecting process -	connectors	
		methods	structure, shape, material or disposition	connectors	Eutomal Javan
		metrious	of bonding areas	Individual bonding area	External layer
					Internal layers
				Plurality of bonding areas	Structure
				Wirebond pads-bonding areas	
	Means for bonding - chip-to-	Bump connectors-	After the connecting process, structure, shape, material or disposition of the bump connectors	Bump connectors formed on an	1
	package, die-attach	manufacturing methods	Bump connectors prior to the	encapsulation of the	
	package, die-attach	manuracturing methods			
			connecting process - structure, shape,	semiconductor or solid-state	
			material or disposition of the	body	-
				Individual bump connector	
		Layer connectors -	Manufacturing methods		
		manufacturing methods	Core members of the layer connector		
		manufacturing methous	Layer connector-Disposition		
			Core members of the connector		
		Wire connectors -	Wire connectors after the connecting		Connecting portions
				Individual wire connector	Disposition
		manufacturing methods	process - structure, shape, material or		Shape
			disposition	Wire connectors Disposition	
P	Pressure-measurement	Measuring fluid pressure by electric or magnetic pressure- sensitive elements			1
		Micro-structural systems			
		Measuring radiation intensity			
F	Radiation-measuring and	with semiconductor detectors			
	letecting	Scintillation-photodiode			
	0	combination			
┢			Integrated circuits	Digital devices	ASIC
					LASER
					LED
			Passive devices, e.g. 2 terminal devices	Optical Diode	OLED
		Device type			
					Photo diode
s	Semiconductor or other solid			Thyristor	
	tate devices to be connected		Three terminal devices	Transistor	BJT
ľ					FET
		MEMS, types of devices			
		Material-semiconductor or solid		Compound semiconductors	III-V
		state bodies	Semiconducting materials	Elemental semiconductors, i.e.	Silicon [Si]
				Group IV	



# Taxonomy (Tabular-2)

					Area CCD imagers
				Charge coupled	Structural or functional details
				imagers	thereof
					Assemblies, i.e. hybrid integration
					MOS based technologies
					Process for coatings or optical
				Manufacture or	elements
				treatment	Thin film technologies, e.g.
					amorphous, poly, micro- or
					nanocrystalline silicon
Semicondu		Devices			Wafer level processing
sensitive to red radiatio		controlled by	Imager	Photodiode	Blooming suppression
short wave		radiation	structures	arrays; MOS	Colour imagers Infra-red imagers
SHOTE WAVE	elength			imagers	X-ray, gamma-ray or corpuscular
				indgers	radiation imagers
					Coatings
					Containers
				Charles and an	Interconnect structures
				Structural or functional	Optical elements or arrangements
				details thereof	associated with the device
					Pixel-elements with integrated
					switching, control, storage or
					amplification elements
		Measuring			
		acceleration,			
		deceleration,			
Speed-		shock			
measurem	ient	Measuring			
		speed by using			
		gyroscopic			
		effect		1	
			Control		
			brightness or	Control of the dynamic range	Charge conversion ratio
			scene		
			Extracting	Combining pixels	
			pixel data	- Solid-state	
			from an		
			image concer	image sensors	
			image sensor		
			image sensor	Applied to dark	
			image sensor	Applied to dark current	
			image sensor	Applied to dark current Correlated	
			image sensor	Applied to dark current	
				Applied to dark current Correlated double or triple	
			Noise	Applied to dark current Correlated double or triple sampling	
			Noise	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure	
		Solid-state	Noise	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise-	
Terrer	ing Hells	Solid-state image sensors	Noise	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure	
Transformi			Noise	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise-	
or analogo	ous		Noise	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise-	sharing a plurality of functions, e.g
or analogo informatio	ous		Noise	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g.	sharing a plurality of functions, e.g output or driving or reset or powe
or analogo informatio electric	ous on into		Noise	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS	sharing a plurality of functions, e.g output or driving or reset or powe lines
or analogo informatio	ous on into		Noise	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g.	sharing a plurality of functions, e.g output or driving or reset or powe lines Pixels within a sensor matrix, e.g.
or analogo informatio electric	ous on into		Noise	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS	sharing a plurality of functions, e.g output or driving or reset or powe lines
or analogo informatio electric	ous on into		Noise processing	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS	sharing a plurality of functions, e.g output or driving or reset or powe lines Pixels within a sensor matrix, e.g. memories
or analogo informatio electric	ous on into		Noise processing Solid-state	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS sensors	sharing a plurality of functions, e.g output or driving or reset or power lines Pixels within a sensor matrix, e.g. memories Readout registers
or analogo informatio electric	ous on into		Noise processing Solid-state image	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS sensors Addressing	sharing a plurality of functions, e.g output or driving or reset or powe lines Pixels within a sensor matrix, e.g. memories Readout registers Timing or clock signal generating
or analogo informatio electric	ous on into		Noise processing Solid-state image sensors	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS sensors Addressing circuits	sharing a plurality of functions, e.g output or driving or reset or powe lines Pixels within a sensor matrix, e.g. memories Readout registers Timing or clock signal generating
or analogo informatio electric	ous on into		Noise processing Solid-state image sensors architecture	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS sensors Addressing circuits Management of	sharing a plurality of functions, e.g output or driving or reset or powe lines Pixels within a sensor matrix, e.g. memories Readout registers Timing or clock signal generating
or analogo informatio electric	ous on into		Noise processing Solid-state image sensors architecture	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS sensors Addressing circuits Management of the power	sharing a plurality of functions, e.g output or driving or reset or powe lines Pixels within a sensor matrix, e.g. memories Readout registers Timing or clock signal generating
or analogo informatio electric	ous on into		Noise processing Solid-state image sensors architecture	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS sensors Addressing circuits Management of the power supply Readout circuits- A/D converters	sharing a plurality of functions, e.g output or driving or reset or powe lines Pixels within a sensor matrix, e.g. memories Readout registers Timing or clock signal generating
or analogo informatio electric	ous on into		Noise processing Solid-state image sensors architecture	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS sensors Addressing circuits Management of the power supply Readout circuits- A/D converters Solid state	sharing a plurality of functions, e.g output or driving or reset or powe lines Pixels within a sensor matrix, e.g. memories Readout registers Timing or clock signal generating
or analogo informatio electric	ous on into		Noise processing Solid-state image sensors architecture	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS sensors Addressing circuits Management of the power supply Readout circuitss A/D converters Solid state image sensors-	sharing a plurality of functions, e.g output or driving or reset or powe lines Pixels within a sensor matrix, e.g. memories Readout registers Timing or clock signal generating
or analogo informatio electric	ous on into	image sensors	Noise processing Solid-state image sensors architecture	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS sensors Addressing circuits Management of the power supply Readout circuits- A/D converters Solid state	sharing a plurality of functions, e.g output or driving or reset or powe lines Pixels within a sensor matrix, e.g. memories Readout registers Timing or clock signal generating
or analogo informatio electric	ous on into	Transforming X-	Noise processing Solid-state image sensors architecture	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS sensors Addressing circuits Management of the power supply Readout circuitss A/D converters Solid state image sensors-	sharing a plurality of functions, e.g output or driving or reset or powe lines Pixels within a sensor matrix, e.g. memories Readout registers Timing or clock signal generating
or analogo informatio electric	ous on into	image sensors	Noise processing Solid-state image sensors architecture & circuits	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS sensors Addressing circuits Management of the power supply Readout circuitss A/D converters Solid state image sensors-	sharing a plurality of functions, e.g output or driving or reset or powe lines Pixels within a sensor matrix, e.g. memories Readout registers Timing or clock signal generating
or analogo informatio electric	ous on into	Transforming X-	Noise processing Solid-state image sensors architecture & circuits Multispectral	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS sensors Addressing circuits Management of the power supply Readout circuitss A/D converters Solid state image sensors-	Pixels within a sensor matrix, e.g. memories Readout registers Timing or clock signal generating
or analogo informatio electric	ous on into	Transforming X- rays	Noise processing Solid-state image sensors architecture & circuits	Applied to dark current Correlated double or triple sampling Excess charges produced by the exposure Reset noise- CMOS Addressed sensors, e.g. MOS or CMOS sensors Addressing circuits Management of the power supply Readout circuitss A/D converters Solid state image sensors-	sharing a plurality of functions, e.g output or driving or reset or power lines Pixels within a sensor matrix, e.g. memories Readout registers Timing or clock signal generating



#### **Contact Us**

Do get in touch with us with your specific needs related to intelligence and decision support on all matters related to technology and its business impact. We will figure the best way to address your needs with an appropriate combination of our technology and reports. We offer a range of tailored solutions and flexible engagement models.



<u>info@relecura.com</u> +1 510 675 0222

www.twitter.com/relecura www.linkedin.com/company/relecura

#### About Relecura

**Relecura** is a full-stack cognitive cloud platform that provides custom intelligence and reports on patent portfolios, technologies and companies. It does this by capturing and organizing the knowledge from various document repositories (patents, scientific literature) and subject matter experts in a flexible and collaborative manner, into a knowledge-base.

**Relecura** offers IP analytics tools and a custom enterprise platform to corporations, law firms, IP services firms, R&D organizations and academic institutions. The enterprise platform integrates the discovery and analysis of public documents with internal company documents. Relecura also has an API to help create custom tools for IP and business intelligence. For more details visit <u>www.relecura.com</u>.

#### Disclaimer

This document is provided for information purposes only and the contents hereof are subject to change without notice. This document, including the information and analysis and any opinion or recommendation, is neither legal advice nor intended for investment purposes. This document is not warranted to be error-free, nor subject to any other warranties or conditions, whether expressed orally or implied in law, including implied warranties and conditions of merchantability or fitness for a particular purpose. Relecura Inc. specifically disclaims any liability with respect to this document and no contractual obligations are formed either directly or indirectly by this document.